| FORM PTO-1449 (REV.7-80) | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | ATTY. DOCKET NO. 500462.04 | APPLICATION NO. ~~Not Yet Assigned~~ 10/626777 |
|---|---|---|---|
| **INFORMATION DISCLOSURE STATEMENT** *(Use several sheets if necessary)* | | APPLICANT(S) Wendell P. Noble | |
| | | FILING DATE Concurrently herewith | GROUP ART UNIT Not Yet Assigned |

## U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|---|---|---|---|---|---|---|---|
| EN | AA | 4,810,667 | 03/07/89 | Zorinsky et al. | 437 | 62 | |
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## FOREIGN PATENT DOCUMENTS

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|---|---|---|---|---|---|---|---|---|
| EN | AJ | JP359232437A | 12/27/84 | Japan | — | — | X | |
| EN | AK | 10135235 | 05/22/98 | Japan | — | — | X | |

## OTHER PRIOR ART *(Including Author, Title, Date, Pertinent Pages, Etc.)*

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*EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

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